TWO MECHANISMS OF ANNEALING OF DIVACANCIES IN IRRADIATED n-Si CRYSTALS

T.A. Pagava, N.T. Bzhalava, N.I. Maisuradze, D.Z. Khocholava, L.S. Chkhartishvili

Georgian Technical University, Department of Physics
(*77, Kostava Str., Tbilisi 0175, Georgia;*
e-mail: tpagava@gtu.ge)

S u m m a r y

We studied n-silicon samples obtained by the floating-zone method and irradiated by 2-MeV electrons with a majority-carrier concentration of 6×10^{13} cm^{-3}. It is shown that, in irradiated n-Si samples, divacancies are annealed by means of two mechanisms: their conversion to other complexes (V_2O or PV_2) or dissociation into separate monovacancies.